

# DSA8508

## Silicon PNP epitaxial planar type

For low frequency output amplification

### ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Contributes to miniaturization of sets, mount area reduction
- Eco-friendly Halogen-free package

### ■ Packaging

DSA8508×0A Radial type : 2000 pcs / carton

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	-30	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-25	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V
Collector current	$I_C$	-5	A
Peak collector current	$I_{CP}$	-8	A
Collector power dissipation *	$P_C$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -1 \text{ mA}, I_B = 0$	-25			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -10 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Forward current transfer ratio *1	$h_{FE}^{*2}$	$V_{CE} = -2 \text{ V}, I_C = -2 \text{ A}$	90		205	—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -3 \text{ A}, I_B = -0.1 \text{ A}$			-1.0	V
Transition frequency	$f_T$	$V_{CE} = -6 \text{ V}, I_C = -50 \text{ mA}$		140		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = -20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			85	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

\*2: Rank classification

Code	P	Q
Rank	P	Q
$h_{FE}$	90 to 135	120 to 205
Marking Symbol	4GP	4GQ

### ■ Package

#### • Code

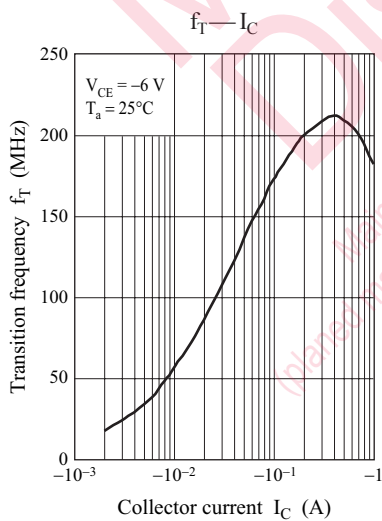
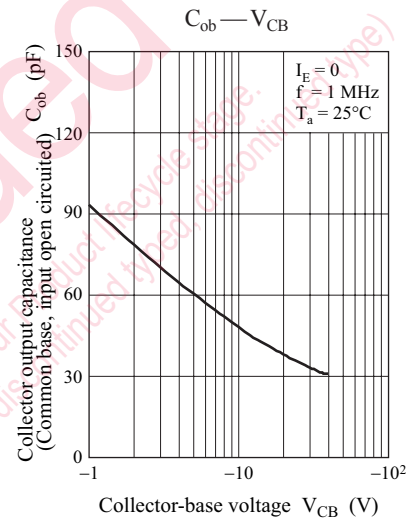
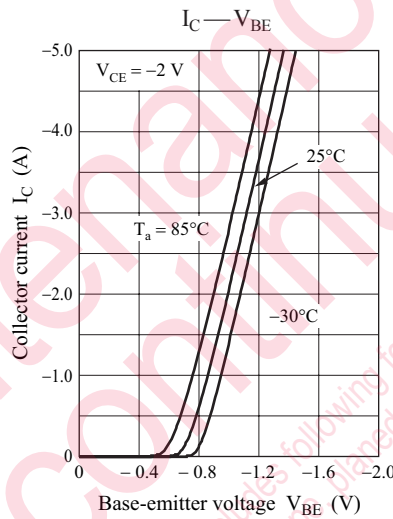
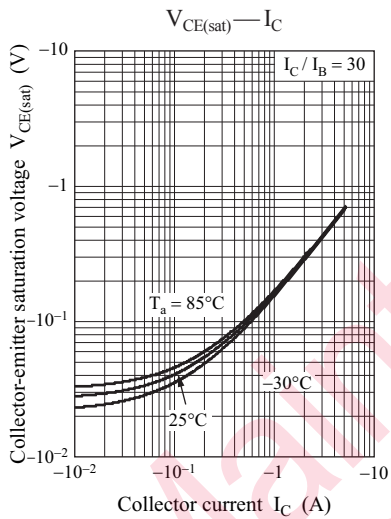
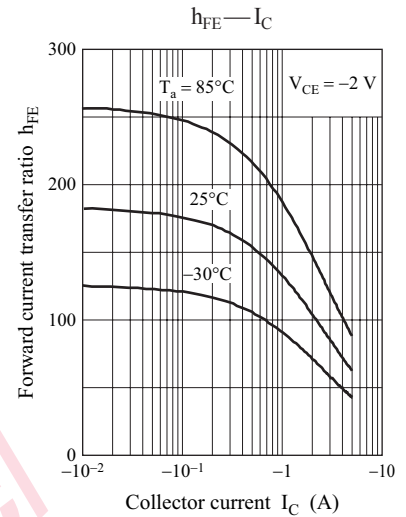
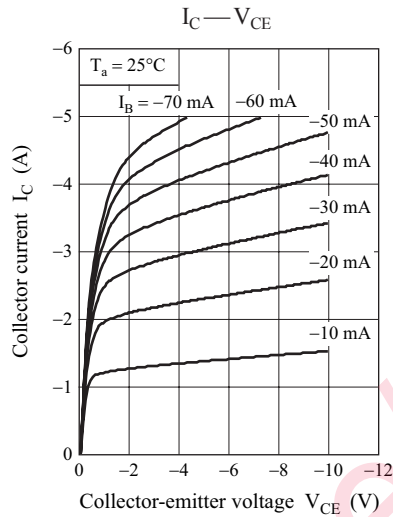
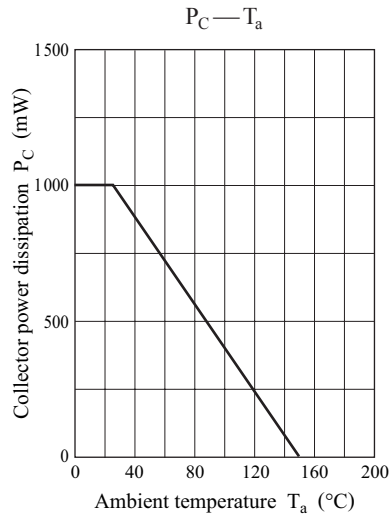
MT-2-A2-B

Package dimension clicks here.→

#### • Pin Name

1. Emitter
2. Collector
3. Base

### ■ Marking Symbol: 4G



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